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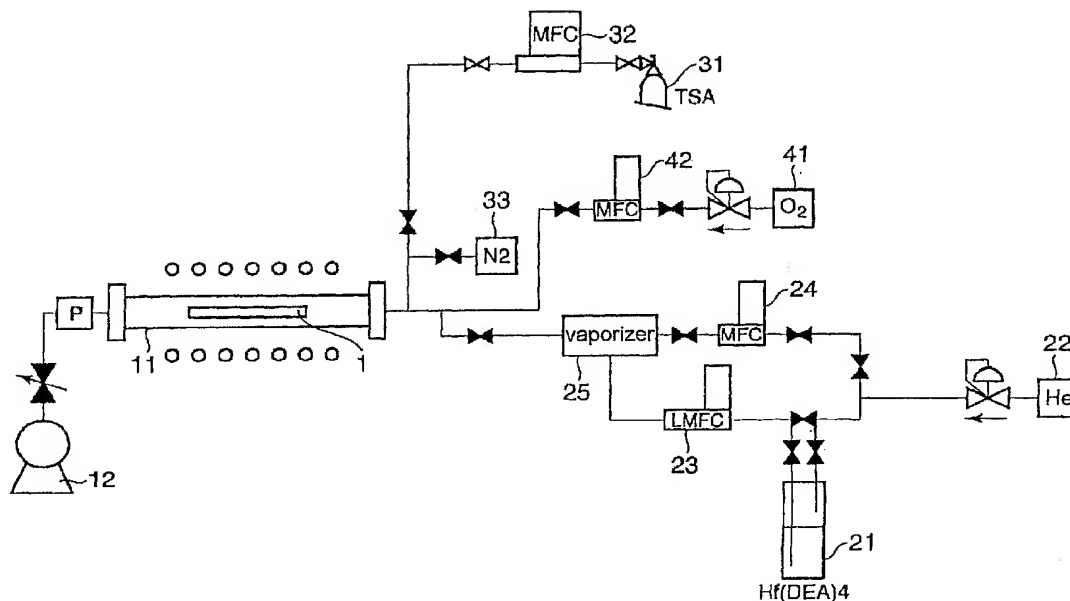
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(54) Title: METHOD FOR FORMING DIELECTRIC OR METALLIC FILMS



(57) Abstract: Method for producing a metal silicon (oxy)nitride by introducing a carbon-free silicon source (for example, $(\text{SiH}_3)_3\text{N}$), a metal precursor with the general formula MX_n (for example, $\text{Hf}(\text{NEt}_2)_4$), and an oxidizing agent (for example, O_2) into a CVD chamber and reacting same at the surface of a substrate. M_2SiN , MSiO and/or MSiON films may be obtained. These films are useful as high k dielectrics films.



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